SEMICONDUCTORS

NOVEMBER03

FETS

MITSUBISHI GaAs FETs





MGF0904 / 2430A

MGF1302 suitable for Low Noise amplifiers, driver amplifiers, & oscillators from 2 – 12GHz. MGF0904 suitable driver for 2-4GHz Power Amplifiers. The MGF1801 is suitable for driver amplifiers up to 10GHz, & the MGF2430A has a 1W output on 10GHz. Datasheets are available on the Mitsubishi Semiconductors WEB site.

www.mitsubishichips.com

Order No	Description	Each
MGF0904	GasFet 13dB gain @1.65GHz	\$50.00
	Pout 28dBm @ 1.65GHz ($\mathbf{10pcs}\ \mathbf{in}$	Stk)
MGF1302	GasFET 11dB gain -	\$7.50
	1.4dB NF@ 4GHz, VDS 3v, ID 10m	A
MGF1801B	GasFET 9dB gain @ 8GHz	\$65.78
	Pout 23dBm @ 8GHz (9pcs in Stk))
MGF2430A-01	GasFET 6.5dB gain @ 14.5GHz	\$112.97
	Pout 30dBm @ 14.5GHz (4pcs in S	itk)

HFET

STANFORD MICRODEVICES



SHF-0189/0589

Stanford Microdevices HFETs, (GaAs Heterostructure FETs) are suitable for building medium poweramplifiers up to 2Watts @ 3GHz. Data sheets are available at <u>www.stanfordmicro.com</u>

May No Longer be Available From Mini-Kits due to No Australian Supplier.

Order No	Description	Each
SHF-0189	HFET 14dB gain @2.4GHz	\$13.80
	Pout 28dBm (640mW) @ 2.4GHz	
SHF-0589	HFET 12dB gain @ 2.4GHz	\$No Stk
	Pout 34.7dBm (3W) @ 2.4GHz	

GaAs MMICS / PHEMTS

HEWLETT PACKARD



The HP GaAs MMIC amplifier uses PHEMT technology with internal self biasing current sources, & offers low noise & excellent gain from 1.5 to 8GHz. Applications include, LNA or gain stages in 2.4GHz to 5.6GHz equipment, including local osc amplifier to +7dBm mixer. The amplifier can be used with a input impedance matching network using a simple wire loop to reduce the noise figure to 1.6dB at 4GHz.

Order No	Description	Each
MGA86576	GaAs MMIC Low Noise Amplifier	\$15.00
	1.5 to 8GHz, gain 23dB	
	NF= 1.8dB @ 4GHz	
	O/P +6dBm @ 4GHz	
	Current Consumption 16mA	

HEWLETT PACKARD PHEMTs



The Hewlett Packard ATF36077 PHEMT is a 2 to 18GHz Ultra Low Noise Transistor. Typical applications include Low noise block front ends for C & KU band Satellite, & High Performance Preamplifiers & Amplifiers for the 1.2 to 24GHz Amateur bands.



Volts DS= 1.5v Current= 10mA (14pcs In Stk)





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HJ FETS



NEC HJ-FETs, are suitable for building medium poweramplifiers up to 4GHz. Devices have been designed for operation on 3.5volt or 5volt supplies. Devices have high linear gain, high PAE up to 50%, & excellent linearity. Data sheets are available at <u>www.cel.com</u>

Order No NE651R479A	Description HJ FET 12dB gain @ 1.9GHz Pout +29.5dBm @ 1.9GHz 5v	Each \$13.10
NE6510179A	HJ FET 10dB gain @ 1.9GHz Pout +35dBm @ 1.9GHz 5V	\$15.55

LIMITED STOCK

GaAs MMICS / PHEMTS

TRANSCOM



The TC3141 is a 2 stage PHEMT MMIC power amplifier. It is designed for 2.4 to 2.5GHz ISM band applications. The MMIC provides a typical gain of 29dB & a 1dB compression of + 33dBm. The MMIC is a standard SO-8 package & requires minimal input & output matching. Devices have high linear gain, high PAE up to 31%, & excellent linearity. Data sheets are available on the Mini-Kits web site.

Order No	Description	Each
TC3141	PHEMT MMIC 29dB gain @ 2.4GHz	\$41.75
	Pout +33dBm @ 2.4GHz 7v 800mA	

Requires Plated through hole PC board for heatsinking

